

## **isc** Silicon NPN Power Transistor

# BU508DX

#### DESCRIPTION

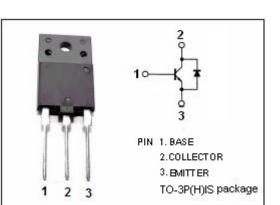
- High Voltage-V<sub>CES</sub>= 1500V(Min.)
- Collector Current-  $I_C = 8.0A$
- Built-in Integrated Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

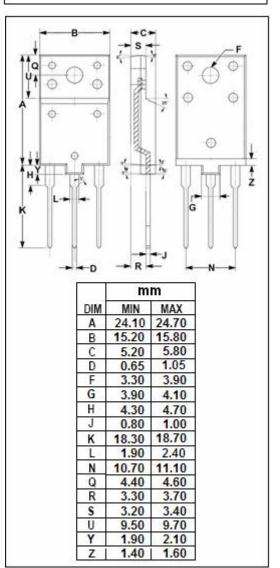
#### **APPLICATIONS**

• Designed for use in large screen color deflection circuits .

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CES</sub>	Collector-Emitter Voltage	1500	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	700	V				
V <sub>EBO</sub>	Emitter-Base Voltage	7	V				
Ic	Collector Current-Continuous	8.0	А				
I <sub>CM</sub>	Collector Current-Peak	15	А				
I <sub>B</sub>	Base Current-Continuous	4	А				
I <sub>BM</sub>	Base Current-Peak	6	А				
Pc	Collector Power Dissipation @Tc=25°C	45	W				
TJ	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature	-65~150	°C				

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C





#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth j-c	Thermal Resistance, Junction to Case	2.8	℃ <b>/W</b>



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### **ELECTRICAL CHARACTERISTICS**

 $T_c=25^{\circ}C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	700			v
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 1.6A			1.0	v
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 1.6A			1.3	v
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V; V <sub>BE</sub> = 0 V <sub>CE</sub> = 1500V; V <sub>BE</sub> = 0; T <sub>C</sub> = 125°C			1.0 2.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5.0V; I <sub>C</sub> = 0			300	mA
hfe	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	6		30	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V		7		MHz
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 4.5A			2.0	V

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